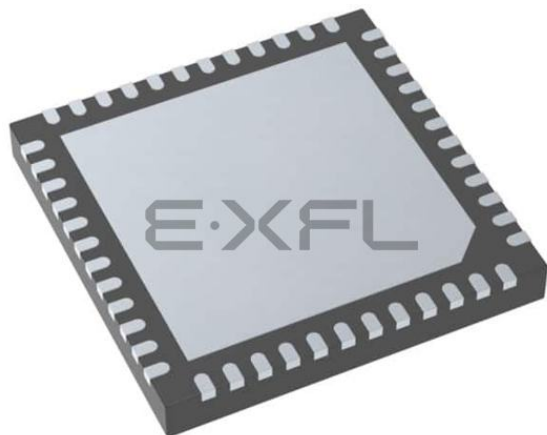




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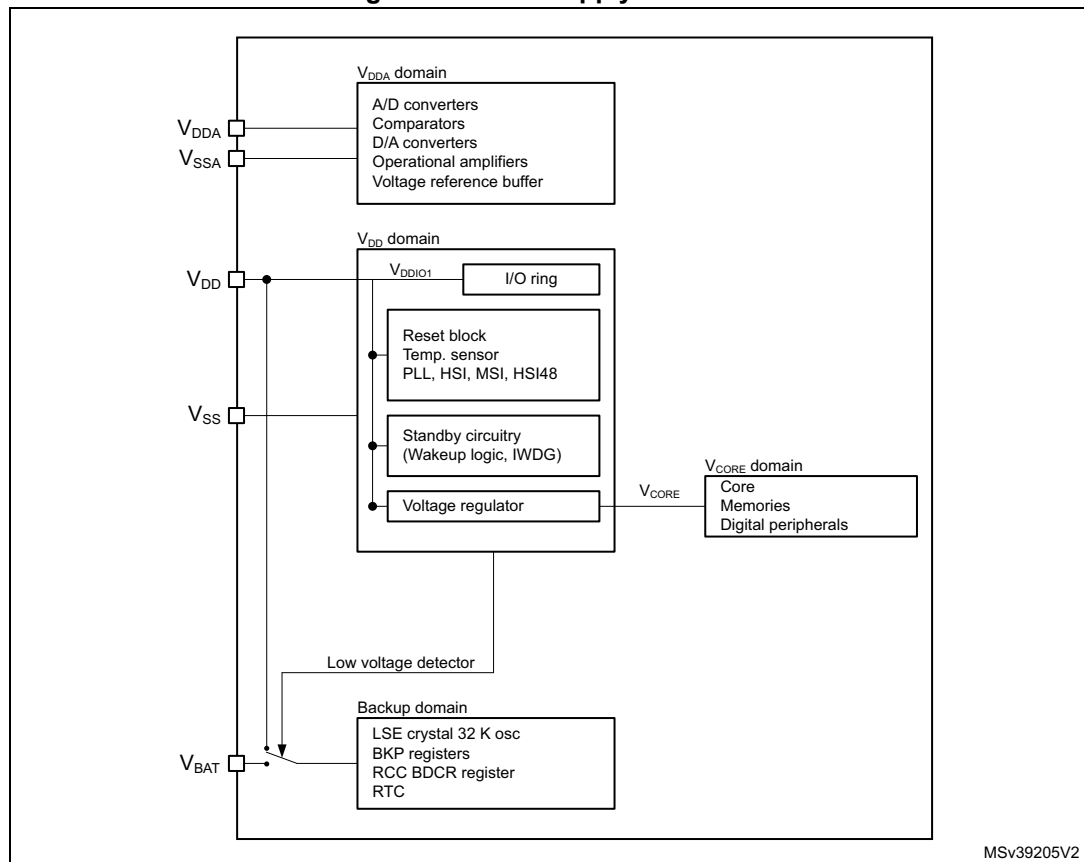
"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	80MHz
Connectivity	CANbus, I ² C, IrDA, LINbus, QSPI, SAI, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, PWM, WDT
Number of I/O	38
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	160K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 10x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-UFQFN Exposed Pad
Supplier Device Package	48-UFQFPN (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l451ceu6

Figure 2. Power supply overview



During power-up and power-down phases, the following power sequence requirements must be respected:

- When V_{DD} is below 1 V, other power supplies (V_{DDA}) must remain below $V_{DD} + 300$ mV.
- When V_{DD} is above 1 V, all power supplies are independent.

During the power-down phase, V_{DD} can temporarily become lower than other supplies only if the energy provided to the MCU remains below 1 mJ; this allows external decoupling capacitors to be discharged with different time constants during the power-down transient phase.



Table 4. STM32L451xx modes overview

Mode	Regulator ⁽¹⁾	CPU	Flash	SRAM	Clocks	DMA & Peripherals ⁽²⁾	Wakeup source	Consumption ⁽³⁾	Wakeup time
Run	MR range 1	Yes	ON ⁽⁴⁾	ON	Any	All	N/A	94 µA/MHz	N/A
	MR range2					All except RNG		85 µA/MHz	
LPRun	LPR	Yes	ON ⁽⁴⁾	ON	Any except PLL	All except RNG	N/A	95 µA/MHz	to Range 1: 4 µs to Range 2: 64 µs
Sleep	MR range 1	No	ON ⁽⁴⁾	ON ⁽⁵⁾	Any	All	Any interrupt or event	27 µA/MHz	6 cycles
	MR range2					All except RNG		27 µA/MHz	
LPSleep	LPR	No	ON ⁽⁴⁾	ON ⁽⁵⁾	Any except PLL	All except RNG	Any interrupt or event	38 µA/MHz	6 cycles
Stop 0	MR Range 1	No	OFF	ON	LSE LSI	BOR, PVD, PVM RTC, IWDG COMPx (x=1,2) DAC1 OPAMPx (x=1) USARTx (x=1...3) ⁽⁶⁾ UART4 ⁽⁶⁾ LPUART1 ⁽⁶⁾ I2Cx (x=1...4) ⁽⁷⁾ LPTIMx (x=1,2) *** All other peripherals are frozen.	Reset pin, all I/Os BOR, PVD, PVM RTC, IWDG COMPx (x=1..2) USARTx (x=1...3) ⁽⁶⁾ UART4 ⁽⁶⁾ LPUART1 ⁽⁶⁾ I2Cx (x=1...4) ⁽⁷⁾ LPTIMx (x=1,2)	125 µA	2.47 µs in SRAM 4.1 µs in Flash
	MR Range 2							125 µA	

Table 6. STM32L451xx peripherals interconnect matrix (continued)

Interconnect source	Interconnect destination	Interconnect action	Run	Sleep	Low-power run	Low-power sleep	Stop 0 / Stop 1	Stop 2
GPIO	TIMx	External trigger	Y	Y	Y	Y	-	-
	LPTIMERx	External trigger	Y	Y	Y	Y	Y	Y ⁽¹⁾
	ADCx DAC1 DFSDM1	Conversion external trigger	Y	Y	Y	Y	-	-

1. LPTIM1 only.

hardware. DFSDM features optional parallel data stream inputs from microcontrollers memory (through DMA/CPU transfers into DFSDM).

DFSDM transceivers support several serial interface formats (to support various $\Sigma\Delta$ modulators). DFSDM digital filter modules perform digital processing according user selected filter parameters with up to 24-bit final ADC resolution.

The DFSDM peripheral supports:

- 4 multiplexed input digital serial channels:
 - configurable SPI interface to connect various SD modulator(s)
 - configurable Manchester coded 1 wire interface support
 - PDM (Pulse Density Modulation) microphone input support
 - maximum input clock frequency up to 20 MHz (10 MHz for Manchester coding)
 - clock output for SD modulator(s): 0..20 MHz
- alternative inputs from 8 internal digital parallel channels (up to 16 bit input resolution):
 - internal sources: device memory data streams (DMA)
- 2 digital filter modules with adjustable digital signal processing:
 - Sinc^x filter: filter order/type (1..5), oversampling ratio (up to 1..1024)
 - integrator: oversampling ratio (1..256)
- up to 24-bit output data resolution, signed output data format
- automatic data offset correction (offset stored in register by user)
- continuous or single conversion
- start-of-conversion triggered by:
 - software trigger
 - internal timers
 - external events
 - start-of-conversion synchronously with first digital filter module (DFSDM1_FLT0)
- analog watchdog feature:
 - low value and high value data threshold registers
 - dedicated configurable Sincx digital filter (order = 1..3, oversampling ratio = 1..32)
 - input from final output data or from selected input digital serial channels
 - continuous monitoring independently from standard conversion
- short circuit detector to detect saturated analog input values (bottom and top range):
 - up to 8-bit counter to detect 1..256 consecutive 0's or 1's on serial data stream
 - monitoring continuously each input serial channel
- break signal generation on analog watchdog event or on short circuit detector event
- extremes detector:
 - storage of minimum and maximum values of final conversion data
 - refreshed by software
- DMA capability to read the final conversion data
- interrupts: end of conversion, overrun, analog watchdog, short circuit, input serial channel clock absence
- “regular” or “injected” conversions:
 - “regular” conversions can be requested at any time or even in continuous mode

Table 16. STM32L451xx pin definitions

Pin Number						Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
UFQFPN48	WLCSP64	LQFP64	UFBGA64	LQFP100	UFBGA100					Alternate functions	Additional functions
-	-	-	-	1	B2	PE2	I/O	FT	-	TRACECK, TIM3_ETR, TSC_G7_IO1, SAI1_MCLK_A, EVENTOUT	-
-	-	-	-	2	A1	PE3	I/O	FT	-	TRACED0, TIM3_CH1, TSC_G7_IO2, SAI1_SD_B, EVENTOUT	-
-	-	-	-	3	B1	PE4	I/O	FT	-	TRACED1, TIM3_CH2, DFSDM1_DATIN3, TSC_G7_IO3, SAI1_FS_A, EVENTOUT	-
-	-	-	-	4	C2	PE5	I/O	FT	-	TRACED2, TIM3_CH3, DFSDM1_CKIN3, TSC_G7_IO4, SAI1_SCK_A, EVENTOUT	-
-	-	-	-	5	D2	PE6	I/O	FT	-	TRACED3, TIM3_CH4, SAI1_SD_A, EVENTOUT	RTC_TAMP3, WKUP3
1	B7	1	B2	6	E2	VBAT	S	-	-	-	-
2	B8	2	A2	7	C1	PC13	I/O	FT	(1) (2)	EVENTOUT	RTC_TAMP1, RTC_TS, RTC_OUT, WKUP2
3	C8	3	A1	8	D1	PC14- OSC32_ IN (PC14)	I/O	FT	(1) (2)	EVENTOUT	OSC32_IN
4	C7	4	B1	9	E1	PC15- OSC32_ OUT (PC15)	I/O	FT	(1) (2)	EVENTOUT	OSC32_OUT
-	-	-	-	10	F2	VSS	S	-	-	-	-
-	-	-	-	11	G2	VDD	S	-	-	-	-
5	D8	5	C1	12	F1	PH0- OSC_IN (PH0)	I/O	FT	-	EVENTOUT	OSC_IN
6	E8	6	D1	13	G1	PH1- OSC_ OUT (PH1)	I/O	FT	-	EVENTOUT	OSC_OUT
7	F8	7	E1	14	H2	NRST	I/O	RST	-	-	-
-	D7	8	E3	15	H1	PC0	I/O	FT_fa	-	LPTIM1_IN1, I2C4_SCL, I2C3_SCL, LPUART1_RX, LPTIM2_IN1, EVENTOUT	ADC1_IN1

Table 16. STM32L451xx pin definitions (continued)

Pin Number						Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
UFQFPN48	WLCSP64	LQFP64	UFBGA64	LQFP100	UFBGA100					Alternate functions	Additional functions
-	-	-	-	86	A6	PD5	I/O	FT	-	USART2_TX, QUADSPI_BK2_IO1, EVENTOUT	-
-	-	-	-	87	B6	PD6	I/O	FT	-	DFSDM1_DATIN1, USART2_RX, QUADSPI_BK2_IO2, SAI1_SD_A, EVENTOUT	-
-	-	-	-	88	A5	PD7	I/O	FT	-	DFSDM1_CKIN1, USART2_CK, QUADSPI_BK2_IO3, EVENTOUT	-
39	B4	55	A5	89	A8	PB3 (JTDO/ TRACE SWO)	I/O	FT_a	(3)	JTDO/TRACESWO, TIM2_CH2, SPI1_SCK, SPI3_SCK, USART1_RTS_DE, SAI1_SCK_B, EVENTOUT	COMP2_INM
40	A4	56	A4	90	A7	PB4 (NJTRST)	I/O	FT_fa	(3)	NJTRST, TIM3_CH1, I2C3_SDA, SPI1_MISO, SPI3_MISO, USART1_CTS, TSC_G2_IO1, SAI1_MCLK_B, EVENTOUT	COMP2_INP
41	C5	57	C4	91	C5	PB5	I/O	FT	-	LPTIM1_IN1, TIM3_CH2, CAN1_RX, I2C1_SMBA, SPI1_MOSI, SPI3_MOSI, USART1_CK, TSC_G2_IO2, COMP2_OUT, SAI1_SD_B, TIM16_BKIN, EVENTOUT	-
42	B5	58	D3	92	B5	PB6	I/O	FT_fa	-	LPTIM1_ETR, I2C1_SCL, I2C4_SCL, USART1_TX, CAN1_TX, TSC_G2_IO3, SAI1_FS_B, TIM16_CH1N, EVENTOUT	COMP2_INP
43	A5	59	C3	93	B4	PB7	I/O	FT_fa	-	LPTIM1_IN2, I2C1_SDA, I2C4_SDA, USART1_RX, UART4_CTS, TSC_G2_IO4, EVENTOUT	COMP2_INM, PVD_IN
44	B6	60	B4	94	A4	PH3- BOOT0 (BOOT0)	I/O	-	-	EVENTOUT	BOOT0

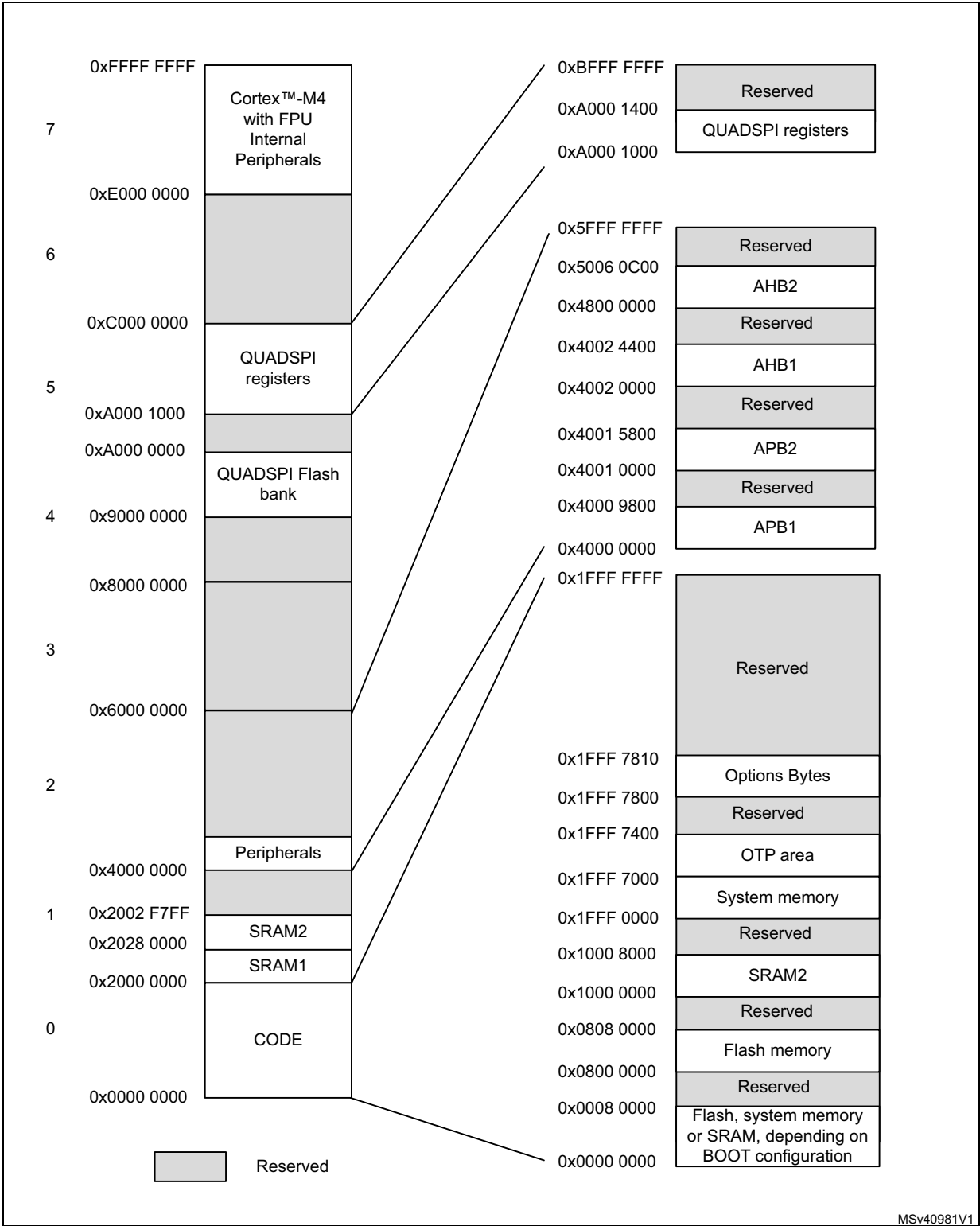
Table 16. STM32L451xx pin definitions (continued)

Pin Number						Pin name (function after reset)	Pin type	I/O structure	Notes	Pin functions	
UFQFPN48	WLCSP64	LQFP64	UFBGA64	LQFP100	UFBGA100					Alternate functions	Additional functions
45	A6	61	B3	95	A3	PB8	I/O	FT_f	-	I2C1_SCL, CAN1_RX, SDMMC1_D4, SAI1_MCLK_A, TIM16_CH1, EVENTOUT	-
46	C6	62	A3	96	B3	PB9	I/O	FT_f	-	IR_OUT, I2C1_SDA, SPI2_NSS, CAN1_TX, SDMMC1_D5, SAI1_FS_A, EVENTOUT	-
-	-	-	-	97	C3	PE0	I/O	FT	-	TIM16_CH1, EVENTOUT	-
-	-	-	-	98	A2	PE1	I/O	FT	-	EVENTOUT	-
47	A7	63	D4	99	D3	VSS	S	-	-	-	-
48	A8	64	E4	100	C4	VDD	S	-	-	-	-

1. PC13, PC14 and PC15 are supplied through the power switch. Since the switch only sinks a limited amount of current (3 mA), the use of GPIOs PC13 to PC15 in output mode is limited:
 - The speed should not exceed 2 MHz with a maximum load of 30 pF
 - These GPIOs must not be used as current sources (e.g. to drive an LED).
2. After a Backup domain power-up, PC13, PC14 and PC15 operate as GPIOs. Their function then depends on the content of the RTC registers which are not reset by the system reset. For details on how to manage these GPIOs, refer to the Backup domain and RTC register descriptions in the RM0394 reference manual.
3. After reset, these pins are configured as JTAG/SW debug alternate functions, and the internal pull-up on PA15, PA13, PB4 pins and the internal pull-down on PA14 pin are activated.

5 Memory mapping

Figure 12. STM32L451xx memory map



MSv40981V1

6.3 Operating conditions

6.3.1 General operating conditions

Table 23. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
f _{HCLK}	Internal AHB clock frequency	-	0	80	MHz
f _{PCLK1}	Internal APB1 clock frequency	-	0	80	
f _{PCLK2}	Internal APB2 clock frequency	-	0	80	
V _{DD}	Standard operating voltage	-	1.71 (1)	3.6	V
V _{DDA}	Analog supply voltage	ADC or COMP used	1.62	3.6	V
		DAC or OPAMP used	1.8		
		VREFBUF used	2.4		
		ADC, DAC, OPAMP, COMP, VREFBUF not used	0		
V _{BAT}	Backup operating voltage	-	1.55	3.6	V
V _{IN}	I/O input voltage	TT_xx I/O	-0.3	V _{DDIOx} +0.3	V
		All I/O except TT_xx	-0.3	Min(Min(V _{DD} , V _{DDA})+3.6 V, 5.5 V) ⁽²⁾⁽³⁾	
P _D	Power dissipation at T _A = 85 °C for suffix 6	LQFP100	-	357	mW
		UFBGA100	-	267	
		LQFP64	-	345	
		UFBGA64	-	308	
		WLCSP64	-	377	
		UFQFPN48	-	690	
P _D	Power dissipation at T _A = 125 °C for suffix 3 ⁽⁴⁾	LQFP100	-	89	mW
		UFBGA100	-	67	
		LQFP64	-	86	
		UFBGA64	-	77	
		WLCSP64	-	94	
		UFQFPN48	-	172	
T _A	Ambient temperature for the suffix 6 version	Maximum power dissipation	-40	85	°C
		Low-power dissipation ⁽⁵⁾	-40	105	
	Ambient temperature for the suffix 3 version	Maximum power dissipation	-40	125	
		Low-power dissipation ⁽⁵⁾	-40	130	
T _J	Junction temperature range	Suffix 6 version	-40	105	°C
		Suffix 3 version	-40	130	

1. When RESET is released functionality is guaranteed down to V_{BOR0} Min.
2. This formula has to be applied only on the power supplies related to the IO structure described by the pin definition table. Maximum I/O input voltage is the smallest value between $\text{Min}(V_{DD}, V_{DDA}) + 3.6 \text{ V}$ and 5.5V.
3. For operation with voltage higher than $\text{Min}(V_{DD}, V_{DDA}) + 0.3 \text{ V}$, the internal Pull-up and Pull-Down resistors must be disabled.
4. If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_{Jmax} (see [Section 7.7: Thermal characteristics](#)).
5. In low-power dissipation state, T_A can be extended to this range as long as T_J does not exceed T_{Jmax} (see [Section 7.7: Thermal characteristics](#)).

6.3.2 Operating conditions at power-up / power-down

The parameters given in [Table 24](#) are derived from tests performed under the ambient temperature condition summarized in [Table 23](#).

Table 24. Operating conditions at power-up / power-down

Symbol	Parameter	Conditions	Min	Max	Unit
t_{VDD}	V_{DD} rise time rate	-	0	∞	$\mu\text{s/V}$
	V_{DD} fall time rate		10	∞	
t_{VDDA}	V_{DDA} rise time rate	-	0	∞	$\mu\text{s/V}$
	V_{DDA} fall time rate		10	∞	

The requirements for power-up/down sequence specified in [Section 3.9.1: Power supply schemes](#) must be respected.

6.3.3 Embedded reset and power control block characteristics

The parameters given in [Table 25](#) are derived from tests performed under the ambient temperature conditions summarized in [Table 23: General operating conditions](#).

Table 25. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions ⁽¹⁾	Min	Typ	Max	Unit
$t_{RSTTEMPO}^{(2)}$	Reset temporization after BOR0 is detected	V_{DD} rising	-	250	400	μs
$V_{BOR0}^{(2)}$	Brown-out reset threshold 0	Rising edge	1.62	1.66	1.7	V
		Falling edge	1.6	1.64	1.69	
V_{BOR1}	Brown-out reset threshold 1	Rising edge	2.06	2.1	2.14	V
		Falling edge	1.96	2	2.04	
V_{BOR2}	Brown-out reset threshold 2	Rising edge	2.26	2.31	2.35	V
		Falling edge	2.16	2.20	2.24	
V_{BOR3}	Brown-out reset threshold 3	Rising edge	2.56	2.61	2.66	V
		Falling edge	2.47	2.52	2.57	
V_{BOR4}	Brown-out reset threshold 4	Rising edge	2.85	2.90	2.95	V
		Falling edge	2.76	2.81	2.86	

Table 34. Current consumption in Low-power sleep modes, Flash in power-down

Symbol	Parameter	Conditions			TYP					MAX ⁽¹⁾					Unit	
		-	Voltage scaling	f _{HCLK}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C		
I _{DD, ALL} (LPSleep)	Supply current in low-power sleep mode	f _{HCLK} = f _{MSI} all peripherals disable			2 MHz	76.5	105	220	410	740	110	175	350	600	1250	µA
					1 MHz	54.0	81.0	195	385	715	81.5	155	325	570	1200	
					400 kHz	28.0	64.5	175	370	695	60.5	130	305	555	1200	
					100 kHz	21.5	55.0	170	360	690	58.5	120	300	550	1200	

1. Guaranteed by characterization results, unless otherwise specified.

Table 35. Current consumption in Stop 2 mode

Symbol	Parameter	Conditions		TYP					MAX ⁽¹⁾					Unit
		-	V _{DD}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	
I _{DD_ALL} (Stop 2)	Supply current in Stop 2 mode, RTC disabled	-	1.8 V	2.05	5.40	19.0	44.0	97.0	4.00	11.5	41.5	100	220	µA
			2.4 V	2.10	5.45	19.0	44.5	98.5	4.05	11.5	42.0	100	225	
			3 V	2.05	5.55	19.5	45.0	100	4.10	12.0	43.0	105	230	
			3.6 V	2.05	5.65	20.0	46.5	105	4.20	12.0	44.0	105	235	
I _{DD_ALL} (Stop 2 with RTC)	Supply current in Stop 2 mode, RTC enabled	RTC clocked by LSI	1.8 V	2.30	5.65	19.0	44.0	97.0	4.50	12.0	42.0	100	220	µA
			2.4 V	2.35	5.80	19.5	44.5	99.0	4.65	12.0	42.5	100	225	
			3 V	2.50	5.90	20.0	45.5	100	4.90	12.5	43.5	105	230	
			3.6 V	2.60	6.15	20.5	47.0	105	5.20	13.0	44.5	105	235	
		RTC clocked by LSE bypassed at 32768 Hz	1.8 V	2.60	6.05	21.0	48.0	97.0	-	-	-	-	-	
			2.4 V	2.55	6.20	21.0	49.0	98.5	-	-	-	-	-	
			3 V	2.80	6.35	21.5	49.5	100	-	-	-	-	-	
			3.6 V	2.85	6.60	22.5	51.5	105	-	-	-	-	-	
		RTC clocked by LSE quartz ⁽²⁾ in low drive mode	1.8 V	2.40	5.70	19.0	44.5	98.0	-	-	-	-	-	
			2.4 V	2.50	5.85	19.5	45.0	99.5	-	-	-	-	-	
			3 V	2.60	6.00	20.0	46.0	100	-	-	-	-	-	
			3.6 V	2.65	6.25	20.5	47.0	105	-	-	-	-	-	

Table 35. Current consumption in Stop 2 mode (continued)

Symbol	Parameter	Conditions		TYP					MAX ⁽¹⁾					Unit
		-	V _{DD}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	
I _{DD_ALL} (wakeup from Stop 2)	Supply current during wakeup from Stop 2 mode	Wakeup clock is MSI = 48 MHz, voltage Range 1. See ⁽³⁾ .	3 V	1.85	-	-	-	-	-	-	-	-	-	mA
		Wakeup clock is MSI = 4 MHz, voltage Range 2. See ⁽³⁾ .	3 V	1.50	-	-	-	-	-	-	-	-	-	
		Wakeup clock is HSI16 = 16 MHz, voltage Range 1. See ⁽³⁾ .	3 V	1.55	-	-	-	-	-	-	-	-	-	

1. Guaranteed based on test during characterization, unless otherwise specified.
2. Based on characterization done with a 32.768 kHz crystal (MC306-G-06Q-32.768, manufacturer JFVNY) with two 6.8 pF loading capacitors.
3. Wakeup with code execution from Flash. Average value given for a typical wakeup time as specified in [Table 42: Low-power mode wakeup timings](#).



Table 39. Current consumption in Shutdown mode (continued)

Symbol	Parameter	Conditions		TYP					MAX ⁽¹⁾					Unit
		-	V _{DD}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	
I _{DD_ALL} (Shutdown with RTC)	Supply current in Shutdown mode (backup registers retained) RTC enabled	RTC clocked by LSE bypassed at 32768 Hz	1.8 V	165	275	950	2600	6550	-	-	-	-	-	nA
			2.4 V	235	370	1150	3100	7650	-	-	-	-	-	
			3 V	325	485	1450	3750	9050	-	-	-	-	-	
			3.6 V	445	655	1900	4800	11500	-	-	-	-	-	
	RTC clocked by LSE quartz ⁽²⁾ in low drive mode		1.8 V	290	410	1050	2550	6700	-	-	-	-	-	
			2.4 V	375	515	1250	3050	7800	-	-	-	-	-	
			3 V	480	645	1550	3700	8800	-	-	-	-	-	
			3.6 V	625	840	1950	4950	11500	-	-	-	-	-	
I _{DD_ALL} (wakeup from Shutdown)	Supply current during wakeup from Shutdown mode	Wakeup clock is MSI = 4 MHz. See ⁽³⁾ .	3 V	1.00	-	-	-	-	-	-	-	-	-	mA

1. Guaranteed by characterization results, unless otherwise specified.

2. Based on characterization done with a 32.768 kHz crystal (MC306-G-06Q-32.768, manufacturer JFVNY) with two 6.8 pF loading capacitors.

3. Wakeup with code execution from Flash. Average value given for a typical wakeup time as specified in [Table 42: Low-power mode wakeup timings](#).

Table 40. Current consumption in VBAT mode

Symbol	Parameter	Conditions		TYP					MAX ⁽¹⁾					Unit
		-	V _{BAT}	25 °C	55 °C	85 °C	105 °C	125 °C	25 °C	55 °C	85 °C	105 °C	125 °C	
I _{DD_VBAT} (VBAT)	Backup domain supply current	RTC disabled	1.8 V	3.00	-	-	-	-	-	-	-	-	-	nA
			2.4 V	4.00	-	-	-	-	-	-	-	-	-	
			3 V	5.00	-	-	-	-	-	-	-	-	-	
			3.6 V	11.0	-	-	-	-	-	-	-	-	-	
		RTC enabled and clocked by LSE bypassed at 32768 Hz	1.8 V	145	165	285	550	-	-	-	-	-	-	
			2.4 V	205	235	370	670	-	-	-	-	-	-	
			3 V	285	315	470	820	-	-	-	-	-	-	
			3.6 V	375	430	715	1350	-	-	-	-	-	-	

1. Guaranteed by characterization results, unless otherwise specified.

Unless otherwise specified, the parameters given are derived from tests performed under the ambient temperature and supply voltage conditions summarized in [Table 23: General operating conditions](#).

Table 63. I/O AC characteristics⁽¹⁾⁽²⁾

Speed	Symbol	Parameter	Conditions	Min	Max	Unit
00	Fmax	Maximum frequency	C=50 pF, 2.7 V ≤ V _{DDIOx} ≤ 3.6 V	-	5	MHz
			C=50 pF, 1.62 V ≤ V _{DDIOx} ≤ 2.7 V	-	1	
			C=50 pF, 1.08 V ≤ V _{DDIOx} ≤ 1.62 V	-	0.1	
			C=10 pF, 2.7 V ≤ V _{DDIOx} ≤ 3.6 V	-	10	
			C=10 pF, 1.62 V ≤ V _{DDIOx} ≤ 2.7 V	-	1.5	
			C=10 pF, 1.08 V ≤ V _{DDIOx} ≤ 1.62 V	-	0.1	
	Tr/Tf	Output rise and fall time	C=50 pF, 2.7 V ≤ V _{DDIOx} ≤ 3.6 V	-	25	ns
			C=50 pF, 1.62 V ≤ V _{DDIOx} ≤ 2.7 V	-	52	
			C=50 pF, 1.08 V ≤ V _{DDIOx} ≤ 1.62 V	-	140	
			C=10 pF, 2.7 V ≤ V _{DDIOx} ≤ 3.6 V	-	17	
			C=10 pF, 1.62 V ≤ V _{DDIOx} ≤ 2.7 V	-	37	
			C=10 pF, 1.08 V ≤ V _{DDIOx} ≤ 1.62 V	-	110	
01	Fmax	Maximum frequency	C=50 pF, 2.7 V ≤ V _{DDIOx} ≤ 3.6 V	-	25	MHz
			C=50 pF, 1.62 V ≤ V _{DDIOx} ≤ 2.7 V	-	10	
			C=50 pF, 1.08 V ≤ V _{DDIOx} ≤ 1.62 V	-	1	
			C=10 pF, 2.7 V ≤ V _{DDIOx} ≤ 3.6 V	-	50	
			C=10 pF, 1.62 V ≤ V _{DDIOx} ≤ 2.7 V	-	15	
			C=10 pF, 1.08 V ≤ V _{DDIOx} ≤ 1.62 V	-	1	
	Tr/Tf	Output rise and fall time	C=50 pF, 2.7 V ≤ V _{DDIOx} ≤ 3.6 V	-	9	ns
			C=50 pF, 1.62 V ≤ V _{DDIOx} ≤ 2.7 V	-	16	
			C=50 pF, 1.08 V ≤ V _{DDIOx} ≤ 1.62 V	-	40	
			C=10 pF, 2.7 V ≤ V _{DDIOx} ≤ 3.6 V	-	4.5	
			C=10 pF, 1.62 V ≤ V _{DDIOx} ≤ 2.7 V	-	9	
			C=10 pF, 1.08 V ≤ V _{DDIOx} ≤ 1.62 V	-	21	

Table 71. ADC accuracy - limited test conditions 3⁽¹⁾(2)(3) (continued)

Sym- bol	Parameter	Conditions ⁽⁴⁾			Min	Typ	Max	Unit
THD	Total harmonic distortion	ADC clock frequency $\leq$ 80 MHz, Sampling rate $\leq$ 5.33 Msps, $1.65\text{ V} \leq V_{\text{DDA}} = V_{\text{REF+}} \leq 3.6\text{ V}$, Voltage scaling Range 1	Single ended	Fast channel (max speed)	-	-69	-67	dB
				Slow channel (max speed)	-	-71	-67	
			Differential	Fast channel (max speed)	-	-72	-71	
				Slow channel (max speed)	-	-72	-71	

1. Guaranteed by design.
2. ADC DC accuracy values are measured after internal calibration.
3. ADC accuracy vs. negative Injection Current: Injecting negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative current.
4. The I/O analog switch voltage booster is enable when $V_{\text{DDA}} < 2.4\text{ V}$ (BOOSTEN = 1 in the SYSCFG_CFGR1 when $V_{\text{DDA}} < 2.4\text{ V}$). It is disable when $V_{\text{DDA}} \geq 2.4\text{ V}$. No oversampling.

6.3.21 Comparator characteristics

Table 76. COMP characteristics⁽¹⁾

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V _{DDA}	Analog supply voltage	-		1.62	-	3.6	V
V _{IN}	Comparator input voltage range	-		0	-	V _{DDA}	
V _{BG} ⁽²⁾	Scaler input voltage	-		V _{REFINT}			
V _{SC}	Scaler offset voltage	-		-	±5	±10	mV
I _{DDA} (SCALER)	Scaler static consumption from V _{DDA}	BRG_EN=0 (bridge disable)		-	200	300	nA
		BRG_EN=1 (bridge enable)		-	0.8	1	µA
t _{START_SCALER}	Scaler startup time	-		-	100	200	µs
t _{START}	Comparator startup time to reach propagation delay specification	High-speed mode	V _{DDA} ≥ 2.7 V	-	-	5	µs
			V _{DDA} < 2.7 V	-	-	7	
		Medium mode	V _{DDA} ≥ 2.7 V	-	-	15	
			V _{DDA} < 2.7 V	-	-	25	
		Ultra-low-power mode		-	-	40	
t _D ⁽³⁾	Propagation delay with 100 mV overdrive	High-speed mode	V _{DDA} ≥ 2.7 V	-	55	80	ns
			V _{DDA} < 2.7 V	-	65	100	
		Medium mode		-	0.55	0.9	µs
		Ultra-low-power mode		-	4	7	
V _{offset}	Comparator offset error	Full common mode range	-	-	±5	±20	mV
V _{hys}	Comparator hysteresis	No hysteresis		-	0	-	mV
		Low hysteresis		-	8	-	
		Medium hysteresis		-	15	-	
		High hysteresis		-	27	-	

SPI characteristics

Unless otherwise specified, the parameters given in [Table 85](#) for SPI are derived from tests performed under the ambient temperature, f_{PCLKx} frequency and supply voltage conditions summarized in [Table 23: General operating conditions](#).

- Output speed is set to OSPEEDRy[1:0] = 11
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: $0.5 \times V_{DD}$

Refer to [Section 6.3.14: I/O port characteristics](#) for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO for SPI).

Table 85. SPI characteristics⁽¹⁾

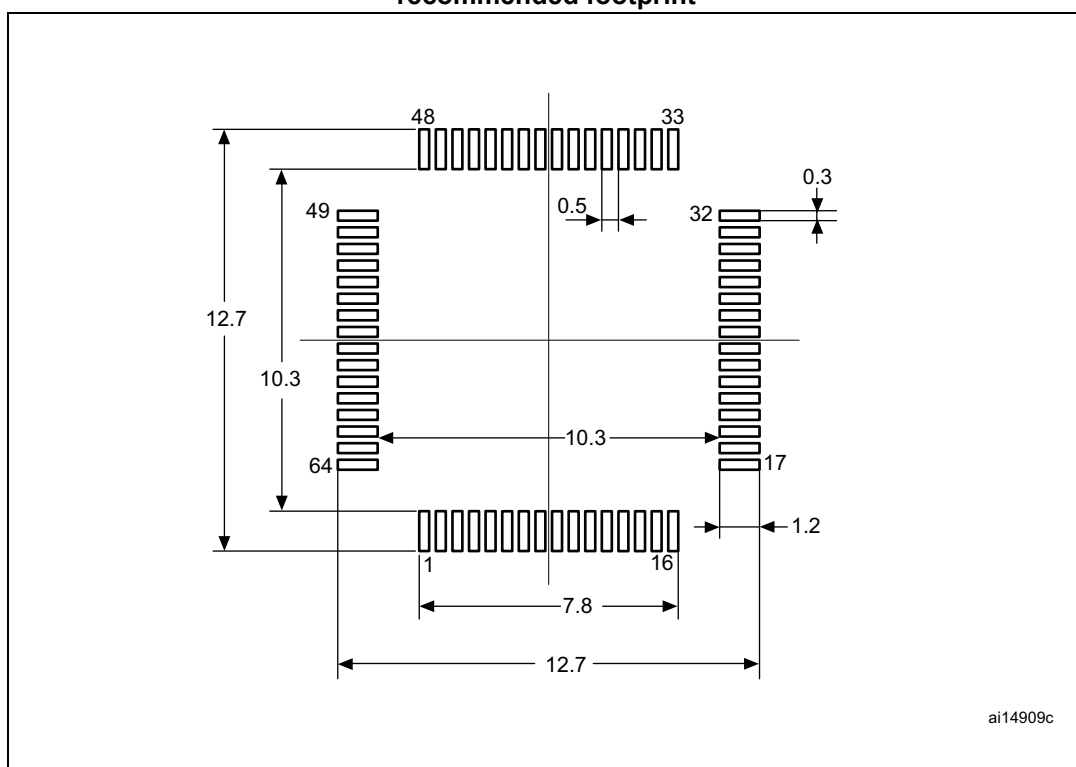
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{SCK} $1/t_c(SCK)$	SPI clock frequency	Master mode receiver/full duplex $2.7 < V_{DD} < 3.6$ V Voltage Range 1	-	-	40	MHz
		Master mode receiver/full duplex $1.71 < V_{DD} < 3.6$ V Voltage Range 1			16	
		Master mode transmitter $1.71 < V_{DD} < 3.6$ V Voltage Range 1			40	
		Slave mode receiver $1.71 < V_{DD} < 3.6$ V Voltage Range 1			40	
		Slave mode transmitter/full duplex $2.7 < V_{DD} < 3.6$ V Voltage Range 1			37 ⁽²⁾	
		Slave mode transmitter/full duplex $1.71 < V_{DD} < 3.6$ V Voltage Range 1			20 ⁽²⁾	
		Voltage Range 2			13	
$t_{su}(NSS)$	NSS setup time	Slave mode, SPI prescaler = 2	$4 \times T_{PCLK}$	-	-	ns
$t_h(NSS)$	NSS hold time	Slave mode, SPI prescaler = 2	$2 \times T_{PCLK}$	-	-	ns
$t_w(SCKH)$ $t_w(SCKL)$	SCK high and low time	Master mode	$T_{PCLK}-2$	T_{PCLK}	$T_{PCLK}+2$	ns
$t_{su}(MI)$	Data input setup time	Master mode	4	-	-	ns
$t_{su}(SI)$		Slave mode	1.5	-	-	
$t_h(MI)$	Data input hold time	Master mode	6.5	-	-	ns
$t_h(SI)$		Slave mode	1.5	-	-	
$t_a(SO)$	Data output access time	Slave mode	9	-	36	ns
$t_{dis}(SO)$	Data output disable time	Slave mode	9	-	16	ns

Table 94. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package mechanical data (continued)

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
E3	-	7.500	-	-	0.2953	-
e	-	0.500	-	-	0.0197	-
K	0°	3.5°	7°	0°	3.5°	7°
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 47. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package recommended footprint



1. Dimensions are expressed in millimeters.

Device marking

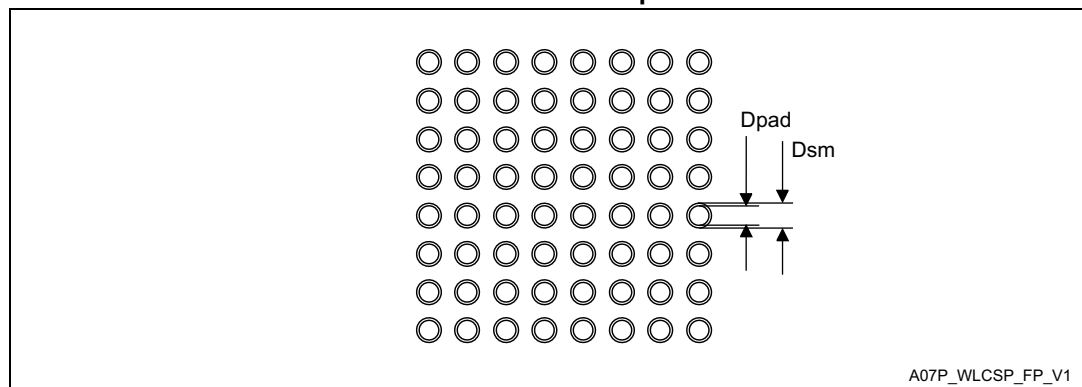
The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Table 97. WLCSP64 - 64-ball, 3.357x3.657 mm 0.4 mm pitch wafer level chip scale mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	0.525	0.555	0.585	0.0207	0.0219	0.0230
A1	-	0.175	-	-	0.0069	-
A2	-	0.380	-	-	0.0150	-
A3	-	0.025	-	-	0.0010	-
b	0.220	0.250	0.280	0.0087	0.0098	0.0110
D	3.322	3.357	3.392	0.1308	0.1322	0.1335
E	3.622	3.657	3.692	0.1426	0.1440	0.1454
e	-	0.400	-	-	0.0157	-
e1	-	2.800	-	-	0.1102	-
e2	-	2.800	-	-	0.1102	-
F	-	0.278	-	-	0.0109	-
G	-	0.428	-	-	0.0169	-
aaa	-	-	0.100	-	-	0.0039
bbb	-	-	0.100	-	-	0.0039
ccc	-	-	0.100	-	-	0.0039
ddd	-	-	0.050	-	-	0.0020
eee	-	-	0.050	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 53. WLCSP64 - 64-pin, 3.357x3.657 mm 0.4 mm pitch wafer level chip scale recommended footprint

1. Dimensions are expressed in millimeters.

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